

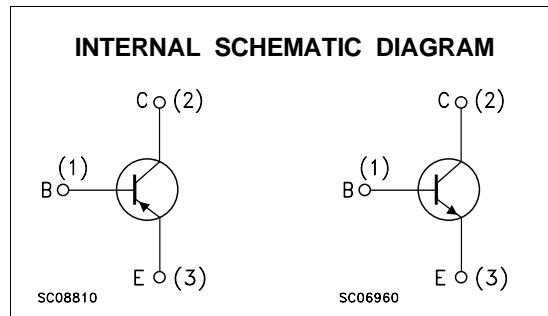
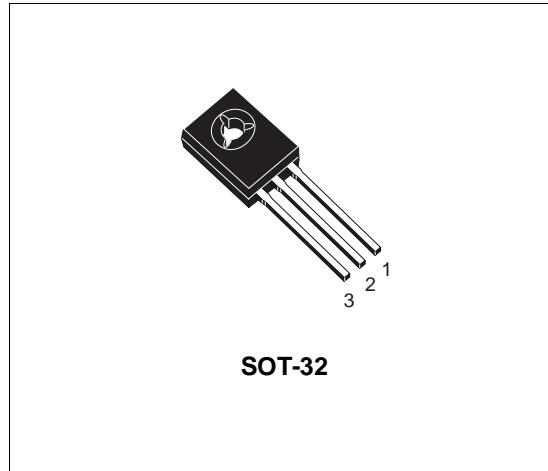
# COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALES TYPES
  - COMPLEMENTARY PNP - NPN DEVICES

## **DESCRIPTION**

The MJE172 (PNP type) and MJE182 (NPN type) are silicon Epitaxial Planar, complementary transistors in Jedec SOT-32 plastic package.

They are designed for low power audio amplifier and low current, high speed switching applications.



## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value		Unit
		NPN	MJE182 <th data-kind="ghost"></th>	
		PNP	MJE172	
V <sub>CBO</sub>	Collector-Emitter Voltage ( $I_B = 0$ )	80		V
V <sub>EBO</sub>	Collector-Base Voltage ( $I_E = 0$ )	100		V
V <sub>CEO</sub>	Base-Emitter Voltage ( $I_C = 0$ )	7		V
I <sub>C</sub>	Collector Current	3		A
I <sub>CM</sub>	Collector Peak Current ( $t_p < 5 \text{ ms}$ )	6		A
I <sub>B</sub>	Base Current	1		A
P <sub>tot</sub>	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$	12.5		W
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$	150		°C

For PNP type voltage and current values are negative.

**THERMAL DATA**

$R_{thj\text{-amb}}$	Thermal Resistance Junction-ambient	Max	83.4	$^{\circ}\text{C/W}$
$R_{thj\text{-case}}$	Thermal Resistance Junction-case	Max	10	$^{\circ}\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_{\text{case}} = 25 \ ^{\circ}\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = \text{rated}$	$V_{CB} = \text{rated}$			0.1	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 7 \text{ V}$				0.1	$\mu\text{A}$
$V_{CEO(\text{sus})^*}$	Collector-Emitter Sustaining Voltage ( $I_B = 0$ )	$I_C = 10 \text{ mA}$		80			V
$V_{CE(\text{sat})^*}$	Collector-Emitter Saturation Voltage	$I_C = 0.5 \text{ A}$ $I_C = 1.5 \text{ A}$ $I_C = 3 \text{ A}$	$I_B = 50 \text{ mA}$ $I_B = 0.15 \text{ A}$ $I_B = 0.6 \text{ A}$			0.3 0.9 1.7	V
$V_{BE(\text{sat})^*}$	Base-Emitter on Voltage	$I_C = 1.5 \text{ A}$ $I_C = 3 \text{ A}$	$I_B = 0.15 \text{ A}$ $I_B = 0.6 \text{ A}$			1.5 2	V
$V_{BE^*}$	Base-Emitter on Voltage	$I_C = 0.5 \text{ A}$	$V_{CE} = 1 \text{ V}$			1.2	V
$h_{FE}$	DC Current Gain	$I_C = 0.1 \text{ A}$ $I_C = 0.5 \text{ A}$ $I_C = 1.5 \text{ A}$	$V_{CE} = 1 \text{ V}$ $V_{CE} = 1 \text{ V}$ $V_{CE} = 1 \text{ V}$	50 30 12		250	
$f_T$	Transistor Frequency	$I_C = 0.1 \text{ A}$ $f = 10 \text{ MHz}$	$V_{CE} = 10 \text{ V}$	50			MHz
$C_{CBO}$	Collector-base Capacitance	$V_{CB} = 10 \text{ V}$ for MJE172 for MJE182				60 40	pF pF

\* Pulsed: Pulse duration = 300 $\mu\text{s}$ , duty cycle  $\leq 1.5\%$   
For PNP type voltage and current values are negative.

SOT-32 (TO-126) MECHANICAL DATA						
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	7.4		7.8	0.291		0.307
B	10.5		10.8	0.413		0.425
b	0.7		0.9	0.028		0.035
b1	0.40		0.65	0.015		0.025
C	2.4		2.7	0.094		0.106
c1	1.0		1.3	0.039		0.051
D	15.4		16.0	0.606		0.630
e		2.2			0.087	
e3		4.4			0.173	
F		3.8			0.150	
G	3		3.2	0.118		0.126
H			2.54			0.100
H2		2.15			0.084	
I		1.27			0.05	
O		0.3			0.011	
V		10°			10°	

